

1N5391 – 1N5399

1.5A SILICON RECTIFIER

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-15							
Dim	Min	Max					
Α	25.4	_					
В	5.50	7.62					
С	0.71	0.864					
D	2.60	3.60					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N 5391	1N 5392	1N 5393	1N 5395	1N 5397	1N 5398	1N 5399	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) $@T_A = 75^{\circ}C$	lo	1.5						A	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	50					A		
Forward Voltage $@I_F = 1.5A$	VFM	1.0						V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	5.0 50						μA	
Typical Junction Capacitance (Note 2)	Cj				30				pF
Typical Thermal Resistance Junction to Ambient (Note 1)	RθJA	50				K/W			
Operating Temperature Range	Tj	-65 to +125					°C		
Storage Temperature Range	Тѕтс	-65 to +150					°C		

*Glass passivated forms are available upon request

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

